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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	20
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 4x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rbagfp-50

Email: info@E-XFL.COM

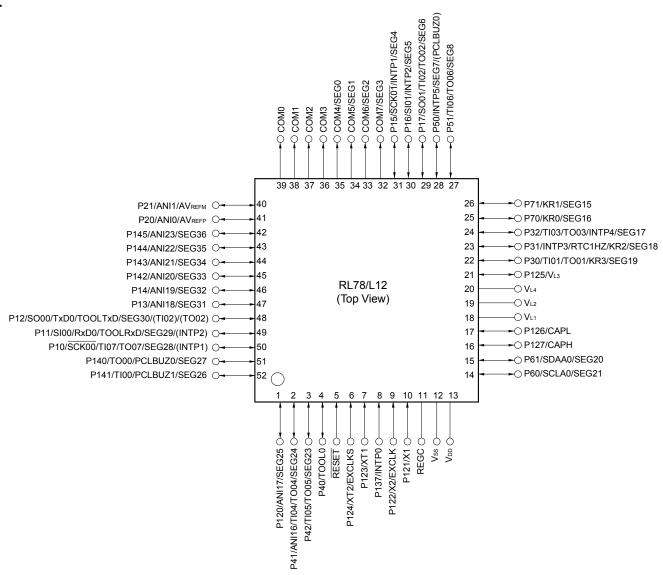
Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/L12 1. OUTLINE

1.3.4 52-pin products

• 52-pin plastic LQFP (10 × 10)

<R>



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

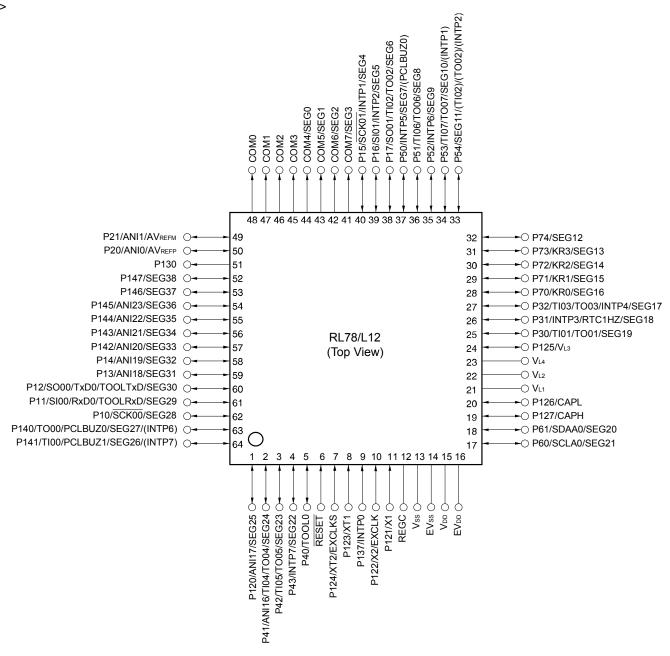
Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

RL78/L12 1. OUTLINE

- 64-pin plastic LQFP (fine pitch) (10 × 10)
- 64-pin plastic LQFP (12 × 12)

<R>

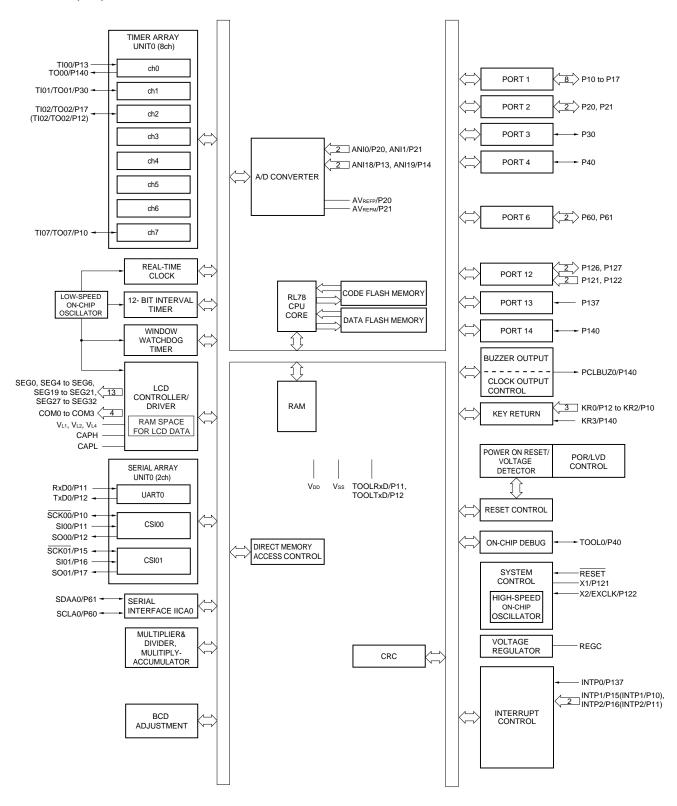


- Cautions 1. Make EVss pin the same potential as Vss pin.
 - 2. Make VDD pin the same potential as EVDD pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD} pins and connect the V_{SS} and EV_{SS} pins to separate ground lines.
 - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

RL78/L12 1. OUTLINE

1.5 Block Diagram

1.5.1 32-pin products



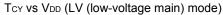
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

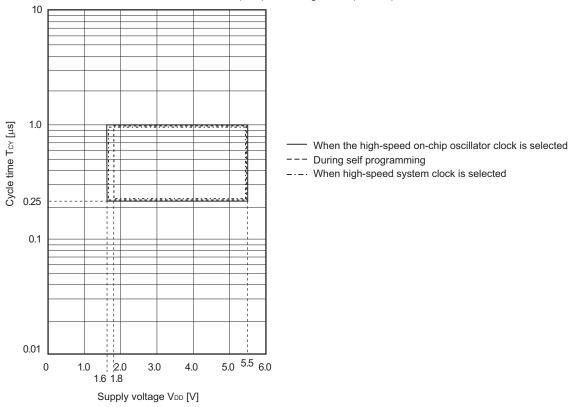
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(2/3)

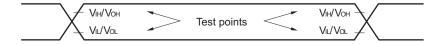
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	1.28	mA
current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.44	1.28	mA
			mode	f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.00	mA
					V _{DD} = 3.0 V		0.40	1.00	mA
			LS (low-	f _{IH} = 8 MHz Note 4	V _{DD} = 3.0 V		260	530	μΑ
			speed main) mode Note 7		V _{DD} = 2.0 V		260	530	μΑ
			LV (low-	f _{IH} = 4 MHz Note 4	$V_{DD} = 3.0 \text{ V}$		420	640	μΑ
			voltage main) mode Note 7		V _{DD} = 2.0 V		420	640	μΑ
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	1.17	mA
			mode	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.00	mA
				V _{DD} = 3.0 V	Resonator connection		0.45	1.17	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.60	mA
				V _{DD} = 5.0 V	Resonator connection		0.26	0.67	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.60	mA
			V _{DD} = 3.0 V	Resonator connection		0.26	0.67	mA	
			LS (low-	$f_{MX} = 8 \text{ MHz}^{\text{Note 3}},$	Square wave input		95	330	μΑ
			speed main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		145	380	μΑ
			mode	$f_{MX} = 8 \text{ MHz}^{\text{Note 3}},$	Square wave input		95	330	μΑ
				V _{DD} = 2.0 V	Resonator connection		145	380	μΑ
			Subsystem	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.31	0.57	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.50	0.76	μΑ
			орстаноп	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.37	0.57	μΑ
				T _A = +25°C	Resonator connection		0.56	0.76	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.46	1.17	μΑ
				T _A = +50°C	Resonator connection		0.65	1.36	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.57	1.97	μΑ
				T _A = +70°C	Resonator connection		0.76	2.16	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.85	3.37	μΑ
				T _A = +85°C	Resonator connection		1.04	3.56	μΑ
	IDD3 Note 6	STOP Note 8	T _A = -40°C				0.17	0.50	μΑ
		mode Note 8	T _A = +25°C	T _A = +25°C			0.23	0.50	μΑ
	TA	T _A = +50°C				0.32	1.10	μΑ	
			T _A = +70°C	A = +70°C			0.43	1.90	μΑ
			T _A = +85°C				0.71	3.30	μΑ

(Notes and Remarks are listed on the next page.)

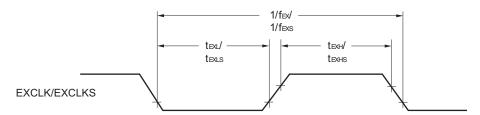




AC Timing Test Points



External System Clock Timing



(2) I²C fast mode

(Ta = -40 to +85°C, 1.6 V \leq EV_{DD} = V_{DD} \leq 5.5 V, Vss = EVss = 0 V)

Parameter	Symbol	(Conditions		HS (high- speed main) Mode		LS (low-speed main) Mode		LV (low- voltage main) Mode	
				MIN.	MAX.	MIN.	MIN.	MAX.	MIN.	
SCLA0 clock frequency	fscL	Fast mode:	2.7 V ≤ EV _{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
		fcLk ≥ 3.5	2.4 V ≤ EV _{DD} ≤ 5.5 V	0	400	0	400	0	400	
		MHz	1.8 V ≤ EV _{DD} ≤ 5.5 V			0	400	0	400	
Setup time of restart condition	tsu:sta	2.7 V ≤ EV _{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		2.4 V ≤ EV _{DD}	≤ 5.5 V	0.6		0.6		0.6		
		1.8 V ≤ EV _{DD}	≤ 5.5 V			0.6		0.6		
Hold time Note 1	thd:sta	2.7 V ≤ EV _{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		2.4 V ≤ EV _{DD}	2.4 V ≤ EV _{DD} ≤ 5.5 V			0.6		0.6		
		1.8 V ≤ EV _{DD} ≤ 5.5 V				0.6		0.6		
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
		2.4 V ≤ EV _{DD}	≤ 5.5 V	1.3		1.3		1.3		
		1.8 V ≤ EV _{DD}	≤ 5.5 V			1.3		1.3		
Hold time when SCLA0 = "H"	t HIGH	2.7 V ≤ EV _{DD}	≤ 5.5 V	0.6		0.6		0.6		μs
		2.4 V ≤ EV _{DD} ≤ 5.5 V		0.6		0.6		0.6		
		1.8 V ≤ EV _{DD}	≤ 5.5 V			0.6		0.6		
Data setup time (reception)	tsu:dat	2.7 V ≤ EV _{DD}	≤ 5.5 V	100		100		100		ns
		2.4 V ≤ EV _{DD}	≤ 5.5 V	100		100		100		
		1.8 V ≤ EV _{DD}	≤ 5.5 V			100		100		
Data hold time (transmission) ^{Note 2}	thd:dat	2.7 V ≤ EV _{DD}	≤ 5.5 V	0	0.9	0	0.9	0	0.9	μs
		2.4 V ≤ EV _{DD}	≤ 5.5 V	0	0.9	0	0.9	0	0.9	
		1.8 V ≤ EV _{DD}	≤ 5.5 V			0	0.9	0	0.9	
Setup time of stop condition	tsu:sto	2.7 V ≤ EV _{DD}	≤ 5.5 V	0.6		0.6		0.6		μs
		2.4 V ≤ EV _{DD}	≤ 5.5 V	0.6		0.6		0.6		
		$1.8 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$ 0.6		0.6						
Bus-free time	t BUF	2.7 V ≤ EV _{DD}	≤ 5.5 V	1.3		1.3		1.3		μs
		2.4 V ≤ EV _{DD}	≤ 5.5 V	1.3		1.3		1.3		
		1.8 V ≤ EV _{DD}	≤ 5.5 V			1.3		1.3		

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

2.7.2 Internal voltage boosting method

(1) 1/3 bias method

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V _{L1}	C1 to C4 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 μF	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V _{L2}	C1 to C4 ^{Note 1} =	0.47 <i>μ</i> F	2 V _{L1} - 0.1	2 VL1	2 V _{L1}	V
Tripler output voltage	V _{L4}	C1 to C4 ^{Note 1} =	0.47 <i>μ</i> F	3 V _{L1} - 0.15	3 VL1	3 V _{L1}	V
Reference voltage setup time Note 2	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C4 ^{Note 1} =	0.47 μF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between V_{L1} and GND
- C3: A capacitor connected between VL2 and GND
- C4: A capacitor connected between V_{L4} and GND
- $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected [by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B] if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

Absolute Maximum Ratings (TA = 25°C)

(2/3)

Parameter	Symbols		Conditions	Ratings	Unit
LCD voltage	V _{L1}	V _{L1} voltage ^{Note 1}		-0.3 to +2.8 and -0.3 to V _{L4} + 0.3	V
	V _{L2}	V _{L2} voltage ^{Note 1}		-0.3 to V _{L4} + 0.3 Note 2	V
	V _{L3}	VL3 voltage ^{Note 1}		-0.3 to V _{L4} + 0.3 Note 2	V
	V _{L4}	V _{L4} voltage ^{Note 1}		-0.3 to +6.5	V
	V _{LCAP}	CAPL, CAPH vol	tage ^{Note 1}	-0.3 to $V_{L4} + 0.3^{Note 2}$	V
VLOUT	VLOUT	COM0 to COM7, SEG0 to	External resistance division method	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
		SEG38,	Capacitor split method	-0.3 to V _{DD} + 0.3 Note 2	
		output voltage	Internal voltage boosting method	-0.3 to V _{L4} + 0.3 Note 2	

- Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 μ F \pm 30%) and connect a capacitor (0.47 μ F \pm 30%) between the CAPL and CAPH pins.
 - 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss: Reference voltage

3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(1/5)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P10 to P17 P70 to P74, P120, P1	•				-3.0 Note 2	mA
		Total of P10 to P14, F	P40 to P43, P120,	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$			-30.0	mA
		P130, P140 to P147		$2.7 \text{ V} \leq \text{EV}_{DD} \leq 4.0 \text{ V}$			-8.0	mA
		(When duty = 70% Note	nen duty = 70%)	$2.4 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V}$			-4.0	mA
		Total of P15 to P17, F	P30 to P32,	$4.0~V \leq EV_{DD} \leq 5.5~V$			-30.0	mA
		P50 to P54, P70 to P7	,	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 4.0 \text{ V}$			-15.0	mA
		(When duty = 70% Not)	$2.4 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V}$			-8.0	mA
		Total of all pins (When duty = 70% Note				-60.0	mA	
	І он2	P20, P21 Per pin					-0.1	mA
			Total of all pins	$2.4~V \leq V_{DD} \leq 5.5~V$			-0.2	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and I_{OH} = -30.0 mA

Total output current of pins = $(-30.0 \times 0.7)/(80 \times 0.01) \approx -26.25$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P10, P12, P15, and P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(2/5)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _{L1}		10 to P17, P30 to P32, P40 P120, P125 to P127, P130				8.5 Note 2	mA
		Per pin for Pe	Per pin for P60, P61				15.0 Note 2	mA
		Total of P10 t	to P14, P40 to P43, P120,	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$			40.0	mA
		P130, P140 to P147 (When duty = 70% N	P130, P140 to P147	2.7 V ≤ EV _{DD} < 4.0 V			15.0	mA
				2.4 V ≤ EV _{DD} < 2.7 V			9.0	mA
		Total of P15 t	to P17, P30 to P32, P50	$4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$			40.0	mA
		to P54, P60, P125 to P127		$2.7 \text{ V} \le \text{EV}_{DD} \le 4.0 \text{ V}$			35.0	mA
		(When duty =		2,4 V ≤ EV _{DD} < 2.7 V			20.0	mA
			Total of all pins (When duty = 70% Note 3)				80.0	mA
	lol2	P20, P21 Per pin					0.4	mA
			Total of all pins	$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$			0.8	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = 40.0 mA

Total output current of pins = $(40.0 \times 0.7)/(80 \times 0.01) \approx 35.0 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(Ta = -40 to +105°C, 2.4 V \leq EV_{DD} = V_{DD} \leq 5.5 V, Vss = EVss = 0 V)

(3/5)

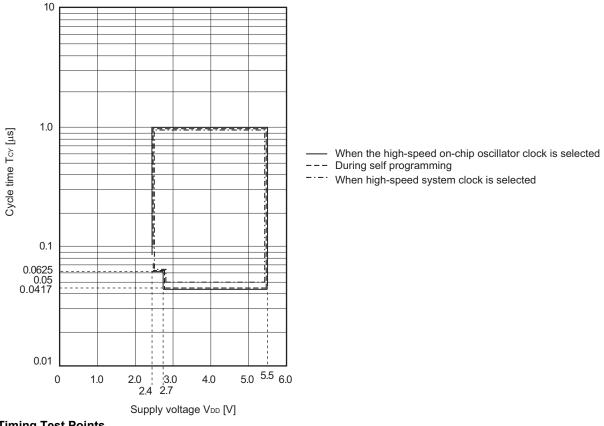
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD}		EV _{DD}	>
	V _{IH2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV _{DD} ≤ 5.5 V	2.2		EV _{DD}	V
			TTL input buffer 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EV _{DD}	V
			TTL input buffer 2.4 V ≤ EV _{DD} < 3.3 V	1.50		EV _{DD}	V
	VIH3	P20, P21		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60, P61		0.7EV _{DD}		EV _{DD}	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	0.8V _{DD}		V_{DD}	V	
Input voltage, low	V _{IL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD}	V
	V _{IL2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	V _{IL3}	P20, P21		0		0.3V _{DD}	V
	VIL4	P60, P61		0		0.3EV _{DD}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS	s, RESET	0		0.2V _{DD}	V

Caution The maximum value of VIH of pins P10, P12, P15, and P17 is EVDD, even in the N-ch open-drain mode.

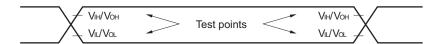
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Minimum Instruction Execution Time during Main System Clock Operation

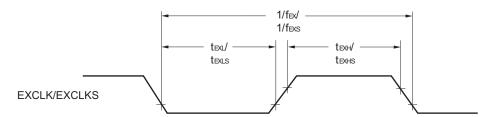
Tcy vs VDD (HS (high-speed main) mode)



AC Timing Test Points

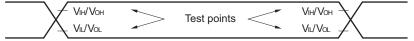


External System Clock Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	d main) Mode	Unit
			MIN.	MAX.	
Transfer rate Note 1				fмск/12	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		2.0	Mbps

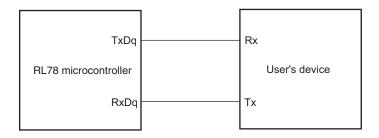
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

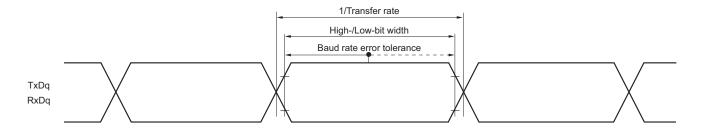
16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

Parameter	Symbol	Cond	litions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		334 Note 1		ns
		2.4 V ≤ EV _{DD} ≤ 5.5 V		500 Note 1		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD} ≤ 5.5 V		tkcy1/2 - 24		ns
	t KL1	$2.7~V \leq EV_{DD} \leq 5.5~V$		tkcy1/2 - 36		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 2	tsik1	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		66		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		113		ns
SIp hold time (from SCKp↑) Note 3	t _{KSI1}	$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		38		ns
Delay time from SCKp↓ to SOp output Note 4	tkso1	C = 30 pF Note 5	$2.4~V \le EV_{DD} \le 5.5~V$		50	ns

Notes 1. Set a cycle of 4/fmck or longer.

- **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS} = 0 \text{ V})$

(2/2)

	Transmission			MIN.		1
	Transmission				MAX.	
		$4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$			Note 1	bps
2.7 V ≤ V _b ≤	$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.0 Note 2	Mbps	
		2.7 V ≤ EV _{DD} < 4.0 V,			Note 3	bps
	$2.3~V \leq V_b \leq 2.7~V$	$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate		1.2 Note 4	Mbps
		2.4 V ≤ EV _{DD} < 3.3 V,	00 – 30 μι , 100 – 2.7 Ks2, Vb – 2.3 V		Note 5	bps
1.6 V ≤ V _b	$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate		0.43 Note 6	Mbps	
			2.4 V ≤ EV _{DD} < 3.3 V,	$maximum \ transfer \ rate$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$ $2.4 \ V \le EV_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$ Theoretical value of the maximum transfer rate	$maximum \ transfer \ rate$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$ $2.4 \ V \le EV_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$ Theoretical value of the	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{ [bps]} \end{aligned}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V})$

Parameter	Symbol	(Conditions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V},$	20 MHz < f _{MCK} ≤ 24 MHz	24/fмск		ns
		$2.7 V \le V_b \le 4.0 V$	8 MHz < fмck ≤ 20 MHz	20/fмск		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/f мск		ns
			fмck ≤ 4 MHz	12/f мск		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$	20 MHz < f _{MCK} ≤ 24 MHz	32/fмск		ns
		$2.3 V \le V_b \le 2.7 V$	16 MHz < f _{MCK} ≤ 20 MHz	28/fмск		ns
			8 MHz < f _{MCK} ≤ 16 MHz	24/fмск		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/f мск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V},$	20 MHz < f _{MCK} ≤ 24 MHz	72/fмск		ns
		$1.6 \text{ V} \le V_b \le 2.0 \text{ V}$	16 MHz < f _{MCK} ≤ 20 MHz	64/ f мск		ns
			8 MHz < f _{MCK} ≤ 16 MHz	52/f мск		ns
			4 MHz < f _{MCK} ≤ 8 MHz	32/fмск		ns
			fмck ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tkH2,	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$	V,	tkcy2/2 - 24		ns
		$2.7 \text{ V} \le \text{EV}_{DD} \le 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		tkcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$	V,	tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsık2	$4.0 \text{ V} \le \text{EV}_{DD} < 5.5 \text{ V}$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$	V,	1/fмск + 40		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2	$4.0 \text{ V} \le \text{EV}_{DD} < 5.5 \text{ V}$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$	V,	1/fмск + 62		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	V,	1/fмск + 62		ns
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$	2.4 V ≤ EV _{DD} < 3.3 V,			ns
Delay time from SCKp↓ to SOp output Note 4	tkso2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ N}$	$V, 2.7 \ V \le V_b \le 4.0 \ V,$ 4 k Ω		2/fмск + 240	ns
		-	$V, 2.3 V \le V_b \le 2.7 V,$		2/fмск + 428	ns
			$V, 1.6 \ V \le V_b \le 2.0 \ V$		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the page after the next page.)

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V \leq EV_{DD} = V_{DD} \leq 5.5 V, Vss = EVss = 0 V, HS (high-speed main) mode)

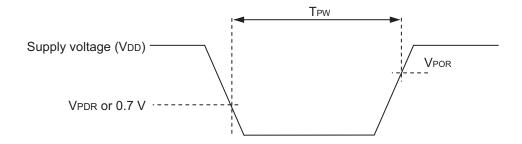
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvтмрs	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

3.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T _{PW}		300			μS

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



(2) 1/4 bias method

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V _{L1} Note 4	C1 to C5 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 μF	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V _{L2}	C1 to C5 ^{Note 1} = 0.47 μ F		2 VL1 - 0.08	2 VL1	2 V _{L1}	V
Tripler output voltage	VL3	C1 to C5 ^{Note 1} =	0.47 μF	3 VL1 – 0.12	3 VL1	3 V _{L1}	V
Quadruply output voltage	V _{L4} Note 4	C1 to $C5^{\text{Note 1}} = 0.47 \ \mu\text{F}$		4 VL1 – 0.16	4 V _{L1}	4 V _{L1}	V
Reference voltage setup time Note 2	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C5 ^{Note 1} =	0.47 <i>μ</i> F	500			ms

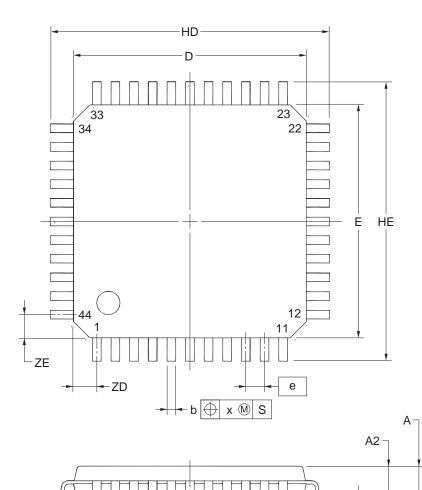
Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between V_{L1} and GND
- C3: A capacitor connected between V_{L2} and GND
- C4: A capacitor connected between $V_{{\mbox{\tiny L3}}}$ and GND
- C5: A capacitor connected between $V_{\text{\tiny L4}}$ and GND
- C1 = C2 = C3 = C4 = C5 = 0.47 μ F±30%
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected [by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B] if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).
- 4. V_{L4} must be 5.5 V or lower.

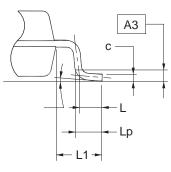
4.2 44-pin Products

R5F10RF8AFP, R5F10RFAAFP, R5F10RFCAFP R5F10RF8GFP, R5F10RFAGFP, R5F10RFCGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



detail of lead end



(UNIT:mm)

ITEM DIMENSIONS

I I E IVI	DIMENSIONS			
D	10.00±0.20			
Е	10.00±0.20			
HD	12.00±0.20			
HE	12.00±0.20			
А	1.60 MAX.			
A1	0.10±0.05			
A2	1.40±0.05			
A3	0.25			
b	$0.37^{+0.08}_{-0.07}$			
С	$0.145^{+0.055}_{-0.045}$			
L	0.50			
Lp	0.60±0.15			
L1	1.00±0.20			
	3°+5°			
е	0.80			
Х	0.20			
у	0.10			

1.00

1.00

NOTE

Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

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